

Small Signal MOSFET

115 mAmps, 60 Volts

N-Channel SOT-323

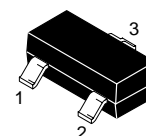
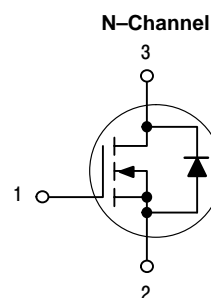
MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0 \text{ M}\Omega$)	V_{DGR}	60	Vdc
Drain Current – Continuous $T_C = 25^\circ\text{C}$ (Note 1.) $T_C = 100^\circ\text{C}$ (Note 1.) – Pulsed (Note 2.)	I_D I_D I_{DM}	± 115 ± 75 ± 800	mAdc
Gate-Source Voltage – Continuous – Non-repetitive ($t_p \leq 50 \mu\text{s}$)	V_{GS} V_{GSM}	± 20 ± 40	Vdc Vpk

THERMAL CHARACTERISTICS

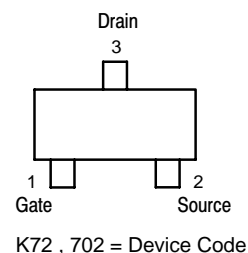
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 3.) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate, (Note 4.) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. The Power Dissipation of the package may result in a lower continuous drain current.
2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.
3. FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$
4. Alumina = $0.4 \times 0.3 \times 0.025 \text{ in}$ in 99.5% alumina.

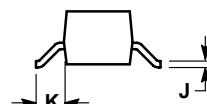
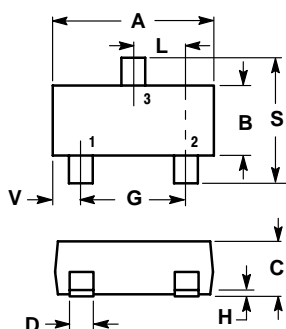


SOT-323

MARKING DIAGRAM & PIN ASSIGNMENT



SOT-323		
Dim	Min	Max
A	1.800	2.200
B	1.150	1.350
C	0.800	1.000
D	0.300	0.400
G	1.200	1.400
H	0.000	0.100
J	0.100	0.250
K	0.350	0.500
L	0.590	0.720
S	2.000	2.400
V	0.280	0.420
All Dimension in mm		



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-Source Breakdown Voltage ($V_{GS} = 0, I_D = 10 \mu\text{A}$)	$V_{(BR)DSS}$	60	—	—	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0, V_{DS} = 60 \text{ Vdc}$)	I_{DSS}	— —	— —	1.0 500	μA μA
Gate-Body Leakage Current, Forward ($V_{GS} = 20 \text{ Vdc}$)	I_{GSSF}	—	—	100	nA
Gate-Body Leakage Current, Reverse ($V_{GS} = -20 \text{ Vdc}$)	I_{GSSR}	—	—	-100	nA

ON CHARACTERISTICS (Note 2.)

Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$)	$V_{GS(th)}$	1.0	—	2.5	Vdc
On-State Drain Current ($V_{DS} \geq 2.0 V_{DS(on)}, V_{GS} = 10 \text{ Vdc}$)	$I_{D(on)}$	500	—	—	mA
Static Drain-Source On-State Voltage ($V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mA}$) ($V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mA}$)	$V_{DS(on)}$	— —	— —	3.75 0.375	Vdc
Static Drain-Source On-State Resistance ($V_{GS} = 10 \text{ V}, I_D = 500 \text{ mA}$) $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$ ($V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mA}$) $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$	$r_{DS(on)}$	— — — —	— — — —	7.5 13.5 7.5 13.5	Ohms
Forward Transconductance ($V_{DS} \geq 2.0 V_{DS(on)}, I_D = 200 \text{ mA}$)	g_{FS}	80	—	—	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{iss}	—	—	50	pF
Output Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{oss}	—	—	25	pF
Reverse Transfer Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{rss}	—	—	5.0	pF

SWITCHING CHARACTERISTICS (Note 2.)

Turn-On Delay Time	(V _{DD} = 25 Vdc, I _D = 500 mA, R _G = 25 Ω , R _L = 50 Ω , V _{gen} = 10 V)	$t_{d(on)}$	—	—	20	ns
Turn-Off Delay Time		$t_{d(off)}$	—	—	40	ns

BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage ($I_S = 11.5 \text{ mA}, V_{GS} = 0 \text{ V}$)	V_{SD}	—	—	-1.5	Vdc
Source Current Continuous (Body Diode)	I_S	—	—	-115	mA
Source Current Pulsed	I_{SM}	—	—	-800	mA

2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

TYPICAL ELECTRICAL CHARACTERISTICS

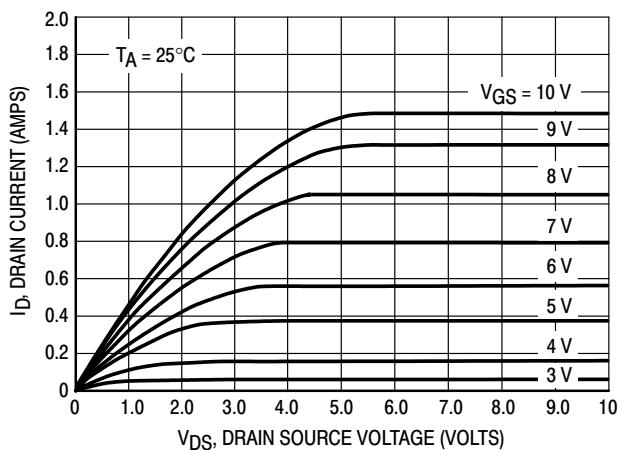


Figure 1. Ohmic Region

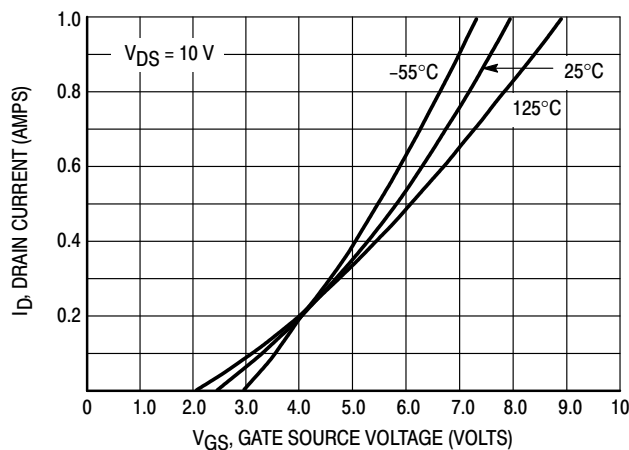


Figure 2. Transfer Characteristics

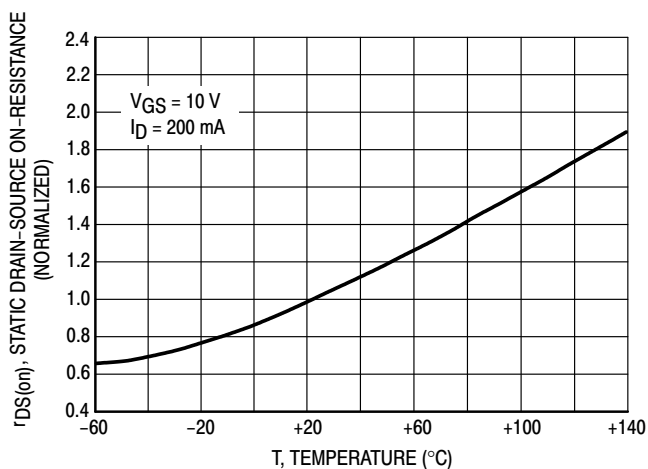


Figure 3. Temperature versus Static Drain-Source On-Resistance

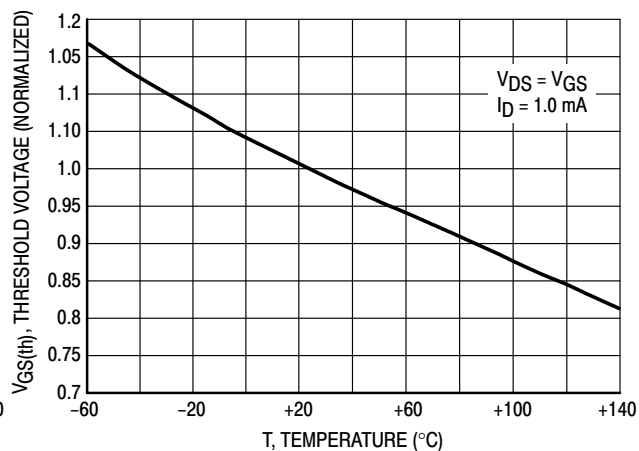


Figure 4. Temperature versus Gate Threshold Voltage